

Amendments to the Claims

1. (Currently Amended): A method of forming a capacitor, comprising:

forming a first capacitor electrode over a semiconductor substrate;

forming a capacitor dielectric region onto the first capacitor electrode, the capacitor dielectric region comprising an exposed oxide-containing surface;

treating the exposed oxide-containing surface of the capacitor dielectric region with at least one of a borane or a silane without depositing any ~~material~~ layer onto the exposed oxide-containing surface during any of said treating; and

after said treating with at least one of the borane or the silane without depositing any ~~material~~ layer onto the exposed oxide-containing surface during any of said treating, then forming a second capacitor electrode over the treated oxide-containing surface, the second capacitor electrode comprising an inner metal surface contacting against the treated oxide-containing surface.

2. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of semiconductive material.

3. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of metal.

4. (Previously Presented): The method of claim 1 wherein the exposed oxide-containing surface comprises hafnium oxide.

5. (Previously Presented): The method of claim 1 wherein the exposed oxide-containing surface comprises aluminum oxide.

6. (Original): The method of claim 1 wherein the treating is with at least one borane.

7. (Original): The method of claim 6 wherein all borane used during the treating is void of halogen.

8. (Original): The method of claim 6 wherein the borane is selected from the group consisting of BH_3 , B_2H_6 , B_4H_{10} , B_5H_9 , B_6H_{10} and $\text{B}_{10}\text{H}_{14}$, and mixtures thereof.

9. (Original): The method of claim 1 wherein the treating is with at least one silane.

10. (Original): The method of claim 9 wherein all silane used during the treating is void of halogen.

11. (Original): The method of claim 9 wherein the silane is selected from the group consisting of SiH_4 , Si_2H_6 , Si_3H_8 and Si_4H_{10} , and mixtures thereof.

Claims 12-15 (Canceled).

16. (Original): The method of claim 1 wherein the treating comprises a temperature from 200°C to 500°C , and a pressure from 1 Torr to 100 Torr.

17. (Original): The method of claim 1 wherein the treating is for at least 1 second.

18. (Original): The method of claim 1 wherein the treating is for at least 10 seconds.

19. (Original): The method of claim 1 wherein the inner metal surface comprises an elemental metal or an alloy of elemental metals.

20. (Original): The method of claim 19 wherein the inner metal surface comprises tungsten.

21. (Original): The method of claim 1 wherein the inner metal surface comprises a conductive metal compound.

22. (Original): The method of claim 21 wherein the inner metal surface comprises TiN.

23. (Original): The method of claim 1 wherein the second capacitor electrode consists essentially of metal.

24. (Currently Amended): The method of claim 1 ~~wherein~~ comprising conducting the treating is to be effective to reduce leakage current of the capacitor than would otherwise occur in the absence of said treating.

25. (Previously Presented): The method of claim 1 wherein the exposed oxide-containing surface comprises OH groups, the treating being effective to passivate said OH groups.

26. (Currently Amended): The method of claim 1 wherein the depositing the second capacitor electrode comprises using a halogen-containing gas, the said treating of the exposed oxide-containing surface of the capacitor dielectric region being effective to reduce halogen incorporation into the capacitor dielectric region than would otherwise occur in the absence of said treating.

Claims 27-31 (Canceled).

32. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of semiconductive material and the second capacitor electrode consists essentially of metal thereby forming an MIS capacitor.

33. (Original): The method of claim 1 wherein the first capacitor electrode consists essentially of metal and the second capacitor electrode consists essentially of metal thereby forming an MIM capacitor.

34. (Currently Amended): A method of forming a capacitor, comprising:

forming a first capacitor electrode over a semiconductor substrate;

forming a capacitor dielectric region onto the first capacitor electrode, the capacitor dielectric region comprising an exposed oxide-containing surface;

treating the exposed oxide-containing surface of the capacitor dielectric region with at least one of a borane or a silane at a temperature from 200°C to 500°C and a pressure from 1 Torr to 100 Torr for at least 1 second, the treating being void of depositing any ~~material~~ layer onto the exposed oxide-containing surface during any of said treating; and

after said treating with at least one of the borane or the silane which is void of depositing any ~~material~~ layer onto the exposed oxide-containing surface during any of said treating, then forming a second capacitor electrode consisting essentially of metal over the treated oxide-containing surface, the second capacitor electrode comprising an inner metal surface contacting against the treated oxide-containing surface.

35. (Previously Presented): The method of claim 34 wherein the exposed oxide-containing surface comprises hafnium oxide.

36. (Previously Presented): The method of claim 34 wherein the exposed oxide-containing surface comprises aluminum oxide.

37. (Original): The method of claim 34 wherein the treating is with at least one borane.

38. (Original): The method of claim 37 wherein all borane used during the treating is void of halogen.

39. (Original): The method of claim 37 wherein the borane is selected from the group consisting of BH_3 , B_2H_6 , B_4H_{10} , B_5H_9 , B_6H_{10} and $\text{B}_{10}\text{H}_{14}$, and mixtures thereof.

40. (Original): The method of claim 34 wherein the treating is with at least one silane.

41. (Original): The method of claim 40 wherein all silane used during the treating is void of halogen.

42. (Original): The method of claim 40 wherein the silane is selected from the group consisting of SiH_4 , Si_2H_6 , Si_3H_8 and Si_4H_{10} , and mixtures thereof.

Claim 43 (Canceled).

44. (Original): The method of claim 34 wherein the treating is for at least 10 seconds.

45. (Original): The method of claim 34 wherein the inner metal surface comprises an elemental metal or an alloy of elemental metals.

46. (Original): The method of claim 45 wherein the inner metal surface comprises tungsten.

47. (Original): The method of claim 34 wherein the inner metal surface comprises a conductive metal compound.

48. (Original): The method of claim 47 wherein the inner metal surface comprises TiN.

49. (Original): The method of claim 34 wherein the treating is effective to reduce leakage current of the capacitor than would otherwise occur in the absence of said treating.

50. (Previously Presented): The method of claim 34 wherein the exposed oxide-containing surface comprises OH groups, the treating being effective to passivate said OH groups.

51. (Previously Presented): The method of claim 34 wherein the depositing the second capacitor electrode comprises using a halogen-containing gas, the treating being effective to reduce halogen incorporation into the capacitor dielectric region than would otherwise occur in the absence of said treating.

Claims 52-124 (Canceled).

125. (Previously Presented): The method of claim 1 wherein the treating is with at least one borane and with at least one silane.

126. (Previously Presented): The method of claim 34 wherein the treating is with at least one borane and with at least one silane.

Claims 127 and 128 (Canceled).

129. (Previously Presented): A method of forming a capacitor, comprising:

forming a first capacitor electrode over a semiconductor substrate;

forming a capacitor dielectric region onto the first capacitor electrode, the capacitor dielectric region comprising an exposed oxide-containing surface;

treating the exposed oxide-containing surface of the capacitor dielectric region with at least one borane and with at least one silane; and

forming a second capacitor electrode over the treated oxide-containing surface, the second capacitor electrode comprising an inner metal surface contacting against the treated oxide-containing surface.